

5. (Twice Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming an electrodeposition frame on a flexible flat metallic substrate, said electrodeposition frame having first metallic layers and second metallic layers for external extension being patterned, wherein said first metallic layers are thicker than said second metallic layers;

contiguously monitoring a plurality of semiconductor elements, each with electrode pads thereon, on said first metallic layers;

wire-bonding the electrode pads to said second metallic layers which are located between said semiconductor elements;

resin-sealing said semiconductor elements mounted on said electrodeposition frame;

removing said metallic substrate to provide a resin sealing body having a bottom so that rear surfaces of the first metallic layers and second metallic layers are flush with the bottom of said resin sealing body;

cutting said resin sealing body into individual semiconductor devices, wherein each device is provided with the first and second metallic layers; and

depositing metallic thin films on portions of the first and second metallic layers that are exposed at the bottom said resin sealing body.